**Product data sheet** 

## 1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel emitter-collector diode in a SOT54 (TO-92) plastic package.

#### 2. Features and benefits

- · High typical DC current gain
- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode

## 3. Applications

- Compact fluorescent lamps (CFL)
- · Low power electronic lighting ballasts
- · Off-line self-oscillating power supplies (SOPS) for battery charging

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	lues		Unit	
Absolute	Absolute maximum rating							
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		7	00		V	
I <sub>c</sub>	collector current	DC	1.5			Α		
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>	2.1		W			
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
h <sub>FE</sub>	DC current gain	$I_{C} = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_{j} = 25 \text{ °C}$		8	17	25		

NPN power transistor with integrated diode

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector	<u> </u>	
3	E	emitter		B — E E sym131
			TO-92 (SOT54)	Symioi

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PHD13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

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# 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	700	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	700	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	400	V
Ic	collector current	DC	1.5	А
I <sub>CM</sub>	peak collector current		3	А
I <sub>B</sub>	base current	DC	0.75	А
I <sub>BM</sub>	peak base current		1.5	А
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>	2.1	W
T <sub>stg</sub>	storage temperature		-65 to 150	°C
T <sub>j</sub>	junction temperature		150	°C
V <sub>EBO</sub>	emitter-base voltage	I <sub>C</sub> = 0 A; I(Emitter) = 10 mA	9	V

## NPN power transistor with integrated diode

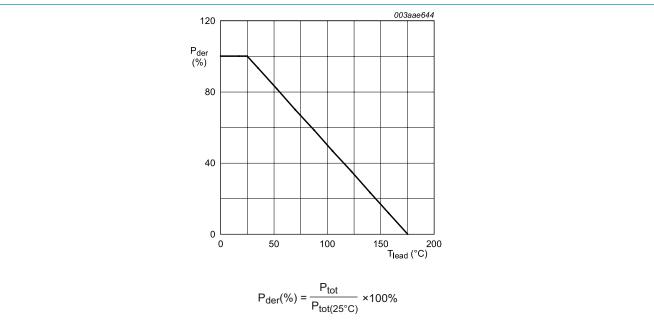


Fig. 1. Normalized total power dissipation as a function of lead temperature

NPN power transistor with integrated diode

### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W

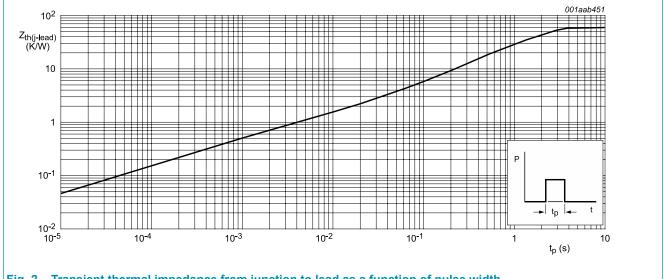


Fig. 2. Transient thermal impedance from junction to lead as a function of pulse width

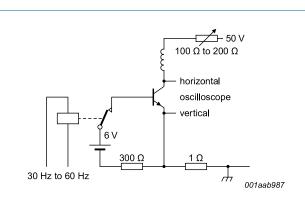
### NPN power transistor with integrated diode

## 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>CES</sub> collector-emitter cut-off current		V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V	-	-	1	mA
	current	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> =100°C	-	-	5	mA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25^{\circ}\text{C}$	-	-	1	mA
$V_{CEOsus}$	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25^{\circ}\text{C}; \underline{\text{Fig. 3}}; \underline{\text{Fig. 4}}$	400	-	-	V
$V_{\sf CEsat}$	collector-emitter	$I_{\rm C} = 0.5  \text{A};  I_{\rm B} = 0.1  \text{A};  T_{\rm lead} = 25  ^{\circ}\text{C}$	-	-	0.5	V
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 0.25 A; T <sub>lead</sub> = 25°C	-	-	1	V
		I <sub>C</sub> = 1.5 A; I <sub>B</sub> = 0.5 A; T <sub>lead</sub> = 25°C	-	-	1.5	V
$V_{BEsat}$	base-emitter saturation	$I_{\rm C} = 0.5  \text{A};  I_{\rm B} = 0.1  \text{A};  T_{\rm lead} = 25  ^{\circ}\text{C}$	-	-	1	V
voltage	voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 0.25 A; T <sub>lead</sub> = 25°C	-	-	1.2	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 0.5 A; T <sub>j</sub> = 25°C	-	-	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.5 A; V <sub>CE</sub> = 2 V; T <sub>j</sub> = 25°C	8	17	25	
		I <sub>C</sub> = 1 A; V <sub>CE</sub> = 2 V; T <sub>j</sub> = 25°C	5	9	15	
Dynamic	characteristics		'			
t <sub>on</sub>	turn-on time	$I_C$ = 1 A; $I_{Bon}$ = 0.2 A; $I_{Boff}$ = -0.2 A; $R_L$ = 75 $\Omega$ ; $T_{Iead}$ = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	1	μs
t <sub>s</sub>	storage time	$I_{C}$ = 1 A; $I_{Bon}$ = 0.2 A; $I_{Boff}$ = -0.2 A; $R_{L}$ = 75 $\Omega$ ; $T_{lead}$ = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	4	μs
		$I_C$ = 1 A; $I_{Bon}$ = 0.2 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{lead}$ = 25 °C; inductive load; <u>Fig. 7</u> ; <u>Fig. 8</u>	-	0.8	-	μs
t <sub>f</sub>	fall time	$I_{C}$ = 1 A; $I_{Bon}$ = 0.2 A; $I_{Boff}$ = -0.2 A; $R_{L}$ = 75 $\Omega$ ; $T_{lead}$ = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	0.7	μs
		$I_{C}$ = 0.5 A; $I_{Bon}$ = 0.1 A; $V_{BB}$ = -5 V; $L_{B}$ = 1 $\mu$ H; $T_{lead}$ = 25 °C; inductive load; <u>Fig. 7</u> ; <u>Fig. 8</u>	-	0.1	-	μs

#### NPN power transistor with integrated diode



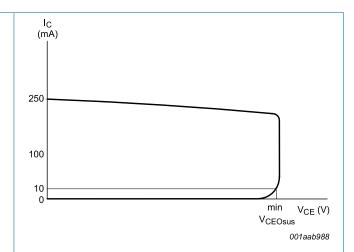
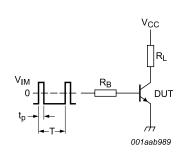


Fig. 3. Test circuit for collector-emitter sustaining voltage

Fig. 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



 $V_{\text{IM}}$  = -6 V to + 8 V;  $V_{\text{CC}}$  = 250 V;  $t_{p}$  = 20  $\mu s$ ;  $\delta$  =  $t_{p}/T$  = 0.01.

 $R_{\text{B}}$  and  $R_{\text{L}}$  calculated from  $I_{\text{Con}}$  and  $I_{\text{Bon}}$  requirements

Fig. 5. Test circuit for resistive load switching

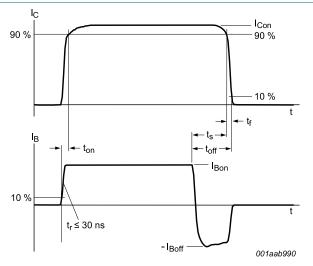
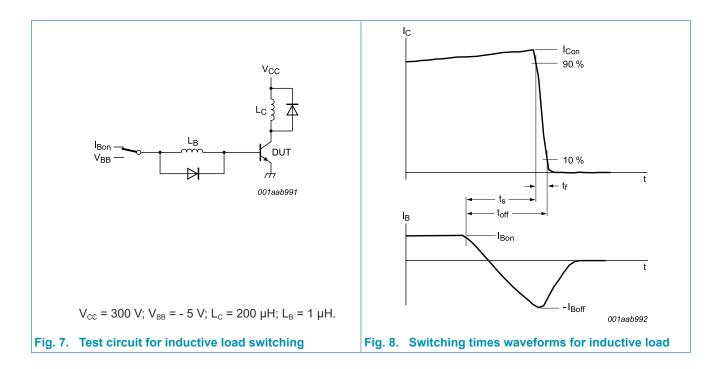


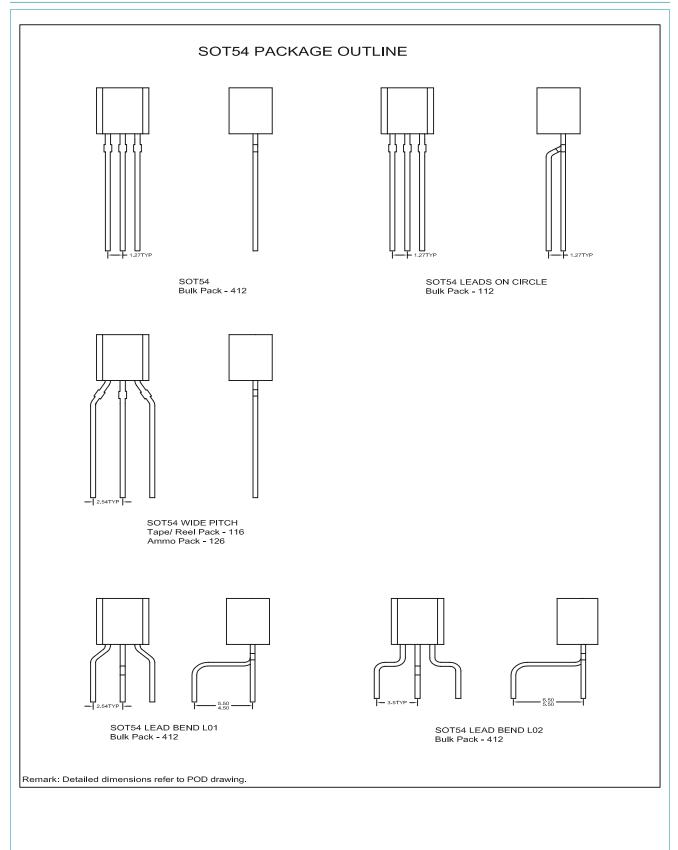
Fig. 6. Switching times waveforms for resistive load

### NPN power transistor with integrated diode



NPN power transistor with integrated diode

# 10. Package outline



NPN power transistor with integrated diode

# 11. Revision history

#### **Table 7. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PHD13003C v.2	20180224	Product data sheet	-	PHD13003C v.1		
Modifications:	Modifications: Change from NXP version to WeEn version					
PHD13003C v.1	20100729	Product data sheet	-	-		

#### NPN power transistor with integrated diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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### NPN power transistor with integrated diode

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### NPN power transistor with integrated diode

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